

CMOS WELL STRUCTURE AND METHOD OF FORMING THE SAME

ABSTRACT OF THE DISCLOSURE

A method for forming a CMOS well structure
5 including forming a plurality of first conductivity type
wells over a substrate, each of the plurality of first
conductivity type wells formed in a respective opening in a
first mask. A cap is formed over each of the first
conductivity type wells, and the first mask is removed.
10 Sidewall spacers are formed on sidewalls of each of the
first conductivity type wells. A plurality of second
conductivity type wells are formed, each of the plurality of
second conductivity type wells are formed between respective
first conductivity type wells. A plurality of shallow
15 trench isolations are formed between the first conductivity
type wells and second conductive type wells. The plurality
of first conductivity type wells are formed by a first
selective epitaxial growth process, and the plurality of
second conductivity type wells are formed by a second
20 selective epitaxial growth process.